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UNDER DEVELOPMENT

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RNP5V7

Transient Voltage Suppressor

Features

- Single Structure
- Suitable to small packages　Chip Size=0.225mmsq
- High ESD protection level
  IEC61000-4-2(ESD)　+/-15kV(Air)　+/-8kV(Contact)

Applications

- LED protections

Item	Characteristics
Wafer size	5inch
Chip Size	225*225um

Maximum Ratings (Ta=25degC)

Symbol	Parameter	Value	Units
P_{pk}	Peak Power Dissipation(tp=8/20us) (*1)	83	W
Ipp	Maximum Peak Pulse Current(tp=8/20us) (*1)	5.5	A
T_{stg}	Storage Temperature Range	-55 to+150	Deg C
T_j	Maximum Junction Temperature (*1)	150	Deg C
Vpp	Electrostatic Discharge IEC61000-4-2 Air Discharge (*1) IEC61000-4-2 Contact Discharge (*1)	 ±15 ±8	 kV kV

(*1) Rating value for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic), mounted on PCB of 1.5cm by 2.5cm.

Electrical Characteristics (Ta=25degC)

Parameter	Symbol	Min	Typ.	Max	Unit	Condition
Breakdown Voltage	V_{BR}	5.7	6.2	6.7	V	I_R =5.0mA
Leakage Current	I_{RM}	-	-	0.1	uA	V_{RWM} =4.0V
Capacitance	C	-	35	-	pF	V=0V 1MHz
Forward Voltage Drop	V_F	-	-	1.2	V	I_F=20mA
Clamping Voltage	Vc	-	-	15	V	Ipp=5.5A (tp=8/20us) *1

*1 Package=SOT-23(front: Au wire 35um, back: Au eutectic)

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Ordering Inforomation

Type	Chip Thickness	Back Metalization	Die Bonding For
RNP5V7V	100um	Au	Eutectic/Ag Paste